

ABSTRACT

The present invention was achieved in order to provide an inspection method, whereby particles adherent to a semiconductor wafer surface, and defects etc. such as SFs, mounds, and dislocations present near the semiconductor wafer surface can be accurately divided according to their types without being influenced by the inspector's ability at a low cost, wherein the wafer is scanned with a laser beam, a scattered or reflected light from the wafer surface is detected in multiple light optics having different detecting angles, and the forms and types of the defects etc. present on the wafer surface are determined based on the ratio of the detected light intensities from the multiple light optics.

09856982-05200